Serial Number: 10/789,736 Filing Date: February 27, 2004

Title: TRANSPARENT AMORPHOUS CARBON STRUCTURE IN SEMICONDUCTOR DEVICES

## IN THE SPECIFICATION

Please delete the paragraphs beginning on page 2, line 1, starting with and including the heading, Summary of the Invention, through page 2, line 5, before the heading Brief Description of the Drawings.

## Please amend the paragraph beginning on page 23, line 17 as follows:

Various embodiments of the invention provide technique techniques to form a transparent amorphous carbon layer. The transparent amorphous carbon layer can be used as a mask for etching certain structure of the device. The amorphous carbon layer can also be a part of a structure of the device for other purposes. In various embodiments, an amorphous carbon layer that is substantially transparent is formed using a process gas containing carbon and a spreading gas to aid in improving the uniformity of the amorphous carbon layer.